

Description

The PDCSM33 is an uni-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The PDCSM33 complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

- 300W peak pulse power(8/20 μs)
- Protects one two uni-directional lines
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test Air discharge: $\pm 30\text{kV}$
Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 25A (8/20 μs)
- RoHS Compliant

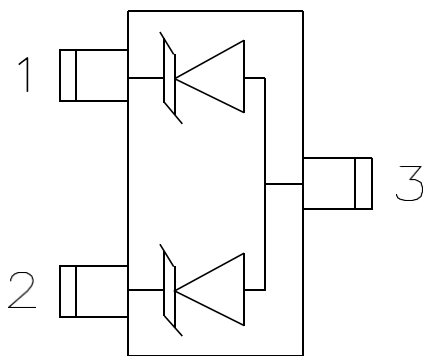
Mechanical Characteristics

- Package: SOT-23
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Peripherals
- Industrial Equipment
- Notebook Computers
- Portable Instrumentation
- Microprocessor Based Equipment
- Cell Phone Handsets and Accessories
- Personal Digital Assistants (PDAs) and Pagers

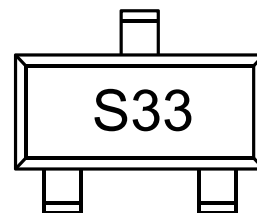
Dimensions and Pin Configuration



SOT23

Circuit and Pin Schematic

Marking Information



S33= Device Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
PDCSM33	S33	3000/Tape & Reel	7 inch

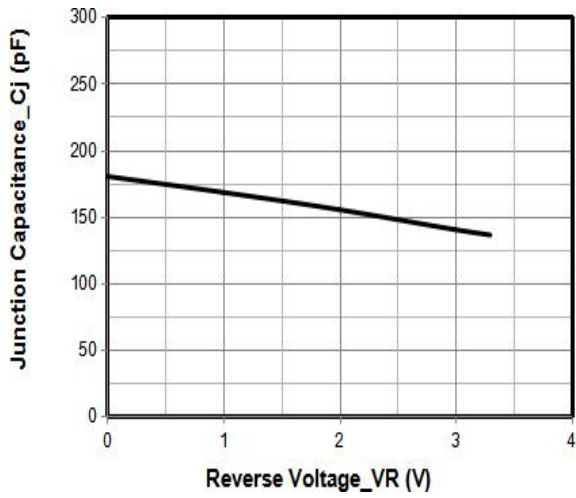
Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	300	W
Peak Pulse Current (8/20µs)	I _{PP}	25	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

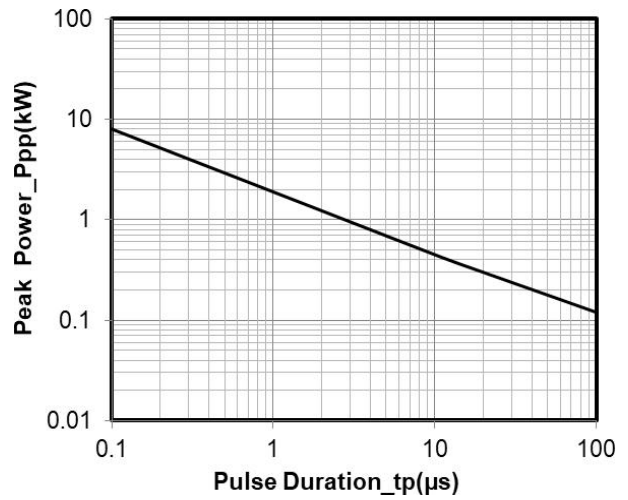
Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Reverse Breakdown Voltage	V _{BR}	3.5			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	µA	V _{RWM} = 3.3V, any I/O pin to ground
Clamping Voltage	V _C			5	V	I _{PP} = 1A (8 x 20µs pulse), any I/O pin to ground
Clamping Voltage	V _C			12	V	I _{PP} = 25A (8 x 20µs pulse), any I/O pin to ground
Junction Capacitance	C _J			200	pF	V _R = 0V, f = 1MHz, any I/O pin to ground

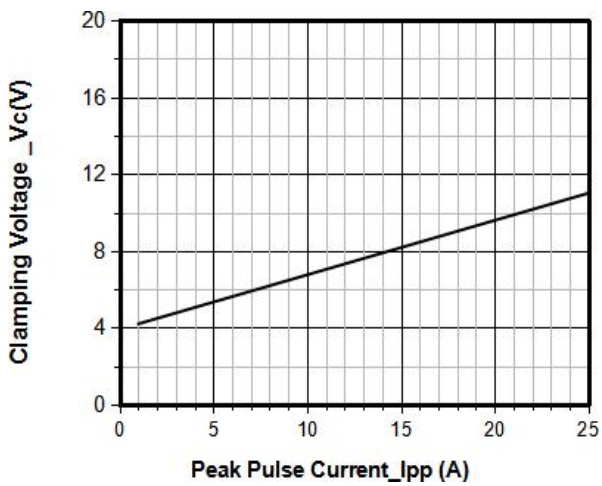
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



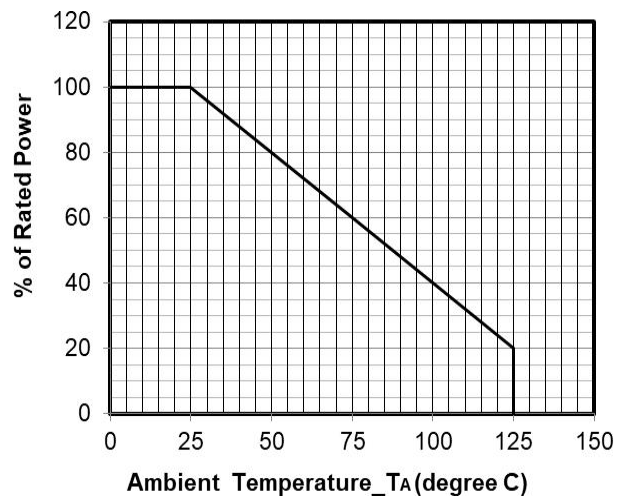
Junction Capacitance vs. Reverse Voltage



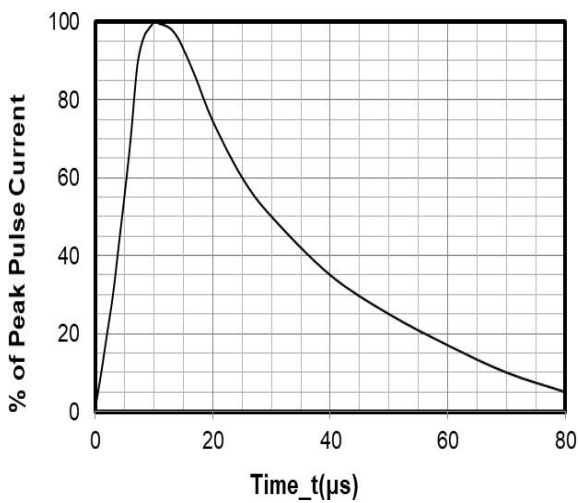
Peak Pulse Power vs. Pulse Time



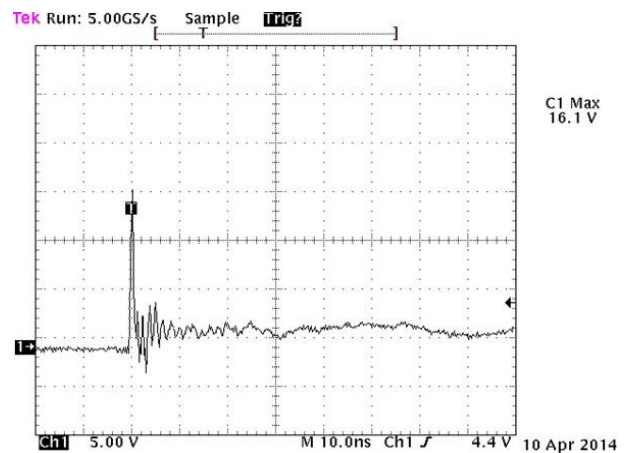
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

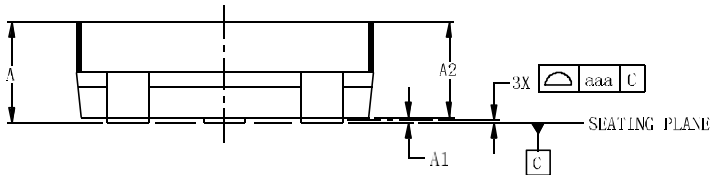
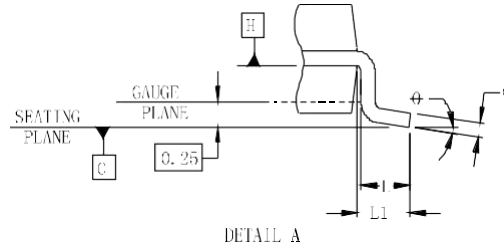
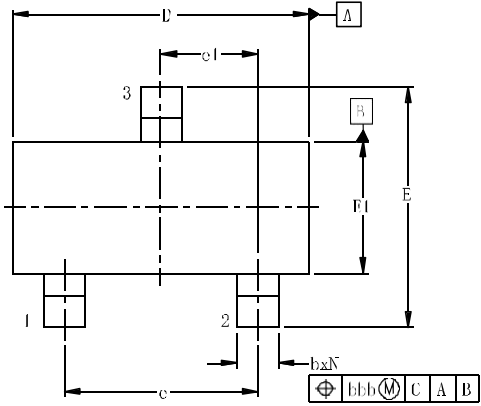


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

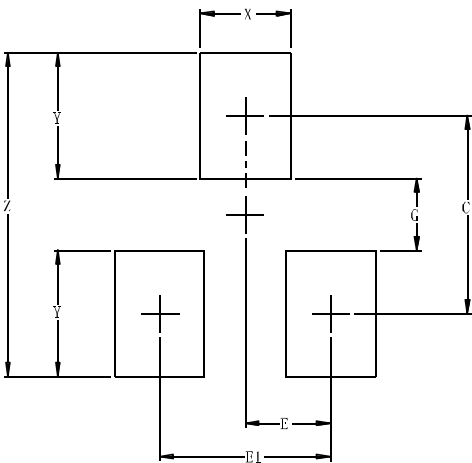
8 kV Contact per IEC61000-4-2

SOT-23 Package Outline Drawing



SYM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	-	0.044	0.89	-	1.12
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
c	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075			1.90BSC		
e1	0.037			0.95BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022			0.55		
N	3			3		
e	0°	-	8°	0°	-	8°
aaa	0.004			0.10		
bbb	0.008			0.20		

Suggested Land Pattern



DIMENSIONS		
SYM	INCHES	MILLIMETERS
C	0.087	2.20
E	0.037	0.95
E1	0.075	1.90
G	0.031	0.80
X	0.039	1.00
Y	0.055	1.40
Z	0.141	3.60